

Patent Appl. No. 08/808,315
Amdt. Dated February 13, 2004
Reply to Office Action of October 20, 2003

Attorney Docket No. 81880.0087
Customer No. 26021

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-19 (Canceled)

20. (Currently amended) A sapphire monocrystal plate for epitaxially growing a semiconductor layer thereon, comprising a sapphire monocrystal having a major face, a working reference plane on a peripheral edge of the plate, the working reference plane being substantially parallel or perpendicular to a plane R of the sapphire monocrystal, wherein the major face is a plane A or a plane C of the sapphire monocrystal and has a surface roughness (Ra) of 0.1 μm or less.

21. (Previously presented): The sapphire monocrystal plate of claim 20, wherein an angle between the working reference plane and the plane R is between -10 to +10 degrees or about 80 to 100 degrees.

22. (Previously presented): The sapphire monocrystal plate of claim 20 further comprising a microcrack line on the major face parallel to the plane R for starting to cleave the plate.

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23. (New) A sapphire monocrystal plate for epitaxially growing a semiconductor layer thereon, comprising a sapphire monocrystal having a major face, a working reference plane on a peripheral edge of the plate, the working reference plane being substantially parallel or perpendicular to a plane R of the sapphire monocrystal, wherein the major face is a plane A or a plane C of the sapphire monocrystal and has a surface roughness (Ra) of 0.1 μm or less, wherein a semiconductor layer produced by epitaxial growth is on the major face.

24. (New): The sapphire monocrystal plate of claim 23, wherein an angle between the working reference plane and the plane R is between -10 to +10 degrees or about 80 to 100 degrees.

25. (New): The sapphire monocrystal plate of claim 23 further comprising a microcrack line on the major face parallel to the plane R for starting to cleave the plate.